ACTIVE SEMICONDUCTIOR FUNCTIONS

	Reference	Туре	Function
AF Circuit			
	IC1 IC2 IC3	NJM2068MD Dream T1 SA572	OP amplifier AF-amplifier and tone-Generator IC Compander IC
RF Circuit			
	Q303 Q304-307 Q308 Q309 Q310 IC5 IC8	2SC4226 2SC5226 2SC4738 2SC4738 2SA1745 MB1511PFV NJU6366	RF-Buffer RF Amplifier Buffer amplifier RF-Power Controller RF-Switch PLL IC PLL/ 9MHz Ref. Oscillator

ACTIVE SEMICONDUCTORS FCCID: JFZT341D

APPENDIX 2

CIRCUITS AND DEVICES TO STABILIZE FREQUENCY

Operating frequency is determined and stabilized by a PLL circuit using a 9MHz crystal-Controlled reference oscillator.

CIRCUIT AND DEVICES TO STABILZE FREQUENCY FCCID: JFZT341D

APPENDIX 3

CIRCUIT TO SUPPRESS SPURIOUS RADIATION AND CONTROL MODULATION

AUDIO CIRCUIT

The audio signal produced by the microphone element is injected into the audio circuit composed of the op amp in IC2, Dream T1, then compressed via the compandor circuit composed o the op amp IC1 and compander IC, IC3, at a 2:1 ratio and is pre-emphasized by AF amp in IC2. The level of the output signal is controlled by the pot VR3 which is injected into the VCO, VCO1.

Output level of the 32.15kHz tone signal that produced by IC2 is controlled by the pot VR4 which is mixed with the audio output signal and injected into the VCO, VCO1

MODULATOR CIRCUIT

The modulator circuit is a direct FM type built around the VCO, VCO1. The modulated output from the VCO is sent to the RF final amplifier which boosts the output to a nominal level of 10mW at RF level low setting and 30mW at RF level Hi setting.

RF PRE-AMPLIFIER & FINAL AMPLIFIER

The 4 transistor amplifier stages, using 2SC4226 and 2SC5226 type transistors, culminating with a nominal transmitter output of 10mW at RF level low setting and 30mW at RF level Hi setting. The output filter comprised of L1303, L304, L1305, L306, C301, C302, C303 & C304 suppresses the output harmonics and output to the antenna.

CIRCUIT TO SUPPRESS SPURIOUS RADIATION & CONTROL MODULATION FCC ID: JFZT341D